

Roll. No:

B. TECH. (SEM I) THEORY EXAMINATION 2020-21 EMERGING DOMAIN IN ELECTRONICS ENGINEERING

Time: 3 Hours Total Marks: 100

Note: 1. Attempt all Sections. If require any missing data; then choose suitably.

SECTION A

1.	Attempt all questions in brief.		= 20
Q no.	Question	Marks	СО
a.	What do you mean by the term doping? Why it is required?	2	1
b.	List any two advantages of modulation.	2	3
c.	Evaluate: $(637)9 = (?)5$	2	2
d.	Draw the VI characteristics of an ideal diode in forward and reverse bias conditions.	2	2
e.	State two differences between microprocessor and microcontroller.	2	3
f.	Why bridge type full wave rectifier is preferred over center tapped full wave rectifier. State two reasons.	2	1
g.	State two differences between FET and BJT.	2	4
h.	Differentiate between avalanche and zener breakdown.	2	1
i.	Find 1's and 2's complement of: 1101001	2	2
j.	State the basic difference between Bluetooth and Wi-Fi technology.	2	2

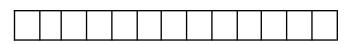
SECTION B

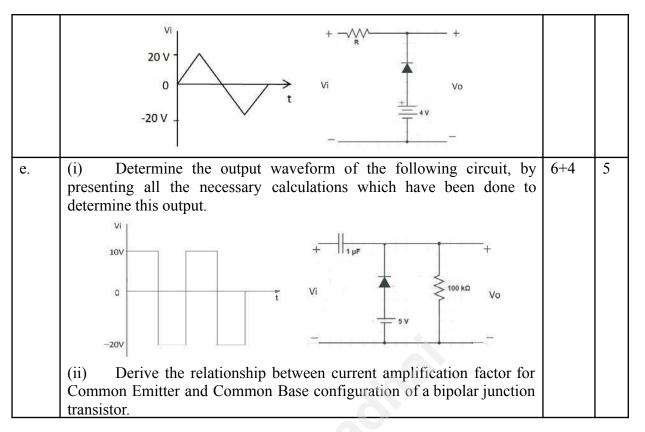
2. Attempt any three of the following:

<u></u>	Attempt any inree of the following:		
Q no.	Question	Marks	СО
a.	 (i) With help of neat circuit diagrams, explain the working of a full wave bridge rectifier. (ii) Define the term ripple factor. What is the value of the ripple factor for a half wave rectifier and a full wave rectifier? 	6+4	3
b.	(i) With help of a neat diagram, explain the working of a voltage doubler circuit.(ii) Write a short note on varactor diode.	6+4	3
c.	For the circuit shown below, determine the value of maximum and minimum zener diode current.	10	4
d.	(i) What are liquid crystal displays? Explain their working with help of a neat diagram.(ii) Determine the output waveform of the following circuit,	3+7	4



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SECTION C

3. Attempt any *one* part of the following:

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Q no.	Question	Marks	СО
a.	Describe the construction of a npn bipolar junction transistor. Draw well	3+5+	4
	labeled input and output characteristics of a npn transistor in Common	2	
	Emitter Configuration. Also mark all the regions of operation		
b.	Give the basic difference between an enhancement and depletion type	2+4+	3
	MOSFET. Discuss the construction of a n channel depletion type	4	
	MOSFET. Also draw its transfer and drain characteristics.		

4. Attempt any *one* part of the following:

_T.	Attempt any one part of the following.		
Q no.	Question	Marks	СО
a.	 (i) What is an operational amplifier? Draw its block diagram. Write the characteristics of an ideal operational amplifier. (ii) With help of the circuit diagram, explain the working of OPAMP as differentiator. 	5+5	3
b.	(i) What do you mean by IOT? Discuss its various components.(ii) Define the following terms:(1) CMRR(2) Peak Inverse Voltage	5+5	3

5. Attempt any *one* part of the following:

Q no.	Question	Marks	СО
a.	Simplify the following function using K map	6+4	4
	$F(A, B, C, D) = \sum (1, 3, 4, 5, 6, 7, 9, 11, 13, 15)$ Also implement the simplified function using basic gates only.		

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I	b. F	PABS showing 7 all the calculations do as directed:	10	0	2
l		(i) For a boolean function of 4 variables, $\Sigma(3,7,11,14,15) = \Pi(?)$			



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(ii) $(110110.011)_2 = (?)_{16}$	
(iii) $(231.36)_{10} = (?)_2$	
(iv) $(11011.10)_2 = (?)_{10}$	
(v)(534)8 = (?)10	

6. Attempt any *one* part of the following:

Q no.	Question	Marks	СО
a.	(i) What do you mean by amplitude modulation? Explain with help	5+5	4
	of proper waveforms.		
	(ii) AM radio transmitter radiates 6 KW power when modulation		
	percentage is 70 %. Determine the carrier power.		
b.	(i) Write a short note on satellite communication system.	5+5	3
	(ii) Differentiate between CDMA and GSM?		

7. Attempt any *one* part of the following:

7.	Attempt any <i>one</i> part of the following:	1361	00
Q no.	Question	Marks	СО
a.	(i) What are universal gates? Why are they called so?	5+5	2
	(ii) Implement XOR gate using NAND gate only.		
b.	Determine the output for the following circuits:	5+5	4
	(i)		
	Rf 10 kΩ		
	V ₁ = 0.2V		
	$V_2 = 0.5V$ V_{out}		
	R2 1 kΩ		
	TRIZ		
	<u>+</u>		
	T = T		
	(ii)		
	200 kΩ		
	+9 V		
	2 kΩ V ₀		
	-9 V		
	V ₁ = 80 μV		

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